

## NJ72L Process

### Silicon Junction Field-Effect Transistor

#### • VHF/UHF Amplifier

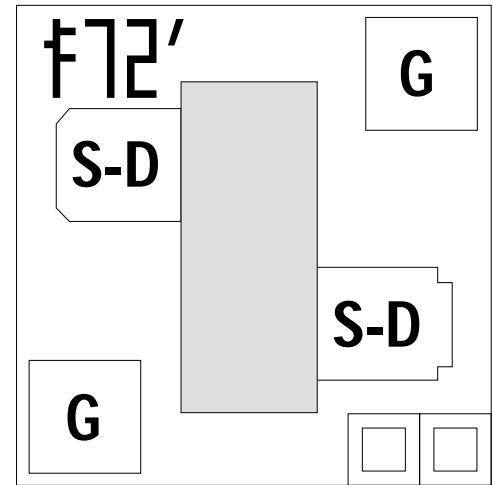
#### Absolute maximum ratings at 25°C free-air temperature.

Gate Current, $I_G$	10 mA
Operating Junction Temperature, $T_j$	+150°C
Storage Temperature, $T_s$	- 65°C to +175°C

#### Devices in this Databook based on the NJ72L Process.

#### Datasheet

U310  
U311  
U350



Die Size = 0.020" X 0.020"  
All Bond Pads = 0.004" Sq.  
Substrate is also Gate.

At 25°C free air temperature:

#### Static Electrical Characteristics

		NJ72L Process						
		Min	Typ	Max	Unit	Test Conditions		
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 20	- 25		V	$I_G = - 1 \mu A, V_{DS} = 0V$		
Reverse Gate Leakage Current	$I_{GSS}$		- 10	- 100	pA	$V_{GS} = - 15V, V_{DS} = 0V$		
Drain Saturation Current (Pulsed)	$I_{DSS}$	5		90	mA	$V_{DS} = 15V, V_{GS} = 0V$		
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 1		- 5.5	V	$V_{DS} = 15V, I_D = 1 nA$		

#### Dynamic Electrical Characteristics

Forward Transconductance	$g_{fs}$		22		mS	$V_{DS} = 15V, V_{GS} = 0V$	$f = 1 kHz$
Drain Source ON Resistance	$r_{ds(on)}$		40		$\Omega$	$I_D = 1 mA, V_{GS} = 0V$	$f = 1 kHz$
Input Capacitance	$C_{iss}$		7		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$
Feedback Capacitance	$C_{rss}$		2.5		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$

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